



## Manipal Institute of Technology, Manipal

(A Constituent Institute of Manipal University)



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## III SEMESTER B.TECH (ELECTRICAL & ELECTRONICS ENGINEERING) MAKE UP EXAMINATIONS, DEC 2015 / JAN 2016

SUBJECT: ANALOG ELECTRONIC CIRCUITS [ELE 209]

## **REVISED CREDIT SYSTEM**

Time: 3 Hours

09 January 2016

MAX. MARKS: 50

## Instructions to Candidates:

- ✤ Answer ANY FIVE FULL questions.
- Missing data may be suitable assumed.
- 1A. In the figure as shown in fig.Q1A, if Vi has a peak of 30 V, then draw the transfer characteristics.
  1B. In the figure as shown in fig.Q1B, identify the diode (V<sub>D</sub>= 0.6 V) based circuit.
  1C. Design a Zener voltage regulator for the following specifications: output voltage = 5V, input voltage = 12 ± 3 V, load current = 20 mA, zener power rating = 500 mW.
- **2A.** Discuss the transconductance of MOSFET. Hence derive the equations governing the relationship between transconductance, current, aspect ratio and gate overdrive voltage of the MOSFET.
- **2B.** Assuming  $\lambda \neq 0$ , draw the small signal model of the circuit shown in Fig.Q2B. **3**
- **2C.** Design the circuit shown in Fig. Q2C for a voltage gain of 5V/V and a power budget of 6mW. Assume that the voltage divider branch consumes 5% of total power and voltage drop across Rs is equal to the overdrive voltage of the transistor. Also assume  $R_D$ = 200 $\Omega$ ,  $V_{TH}$  = 0.4 V, µnCox = 200 µA/V2,  $\lambda$ =0.
- **3A.** For the NMOS common source amplifier shown in Fig. Q3A, the transistor parameters are:  $V_{th} = 0.8 \text{ V}$ ,  $\mu_n C_{ox} (W/2L) = 1 \text{ mA/V}^2$ ,  $V_{DD} = 5 \text{ V}$ ,  $R_s = 1 \text{ k}\Omega$ ,  $R_D = 4 \text{ k}\Omega$ ,  $R_1 = 225 \text{ k}\Omega$ ,  $R_2 = 175 \text{ k}\Omega$ . Calculate the quiescent values  $I_{DQ}$  and  $V_{DSQ}$ . Draw the small signal model and hence determine the small signal gain for  $R_L$  is infinite. Neglect Channel length modulation.
- **3B.** Draw the BJT based voltage devider circuit and derive expression for stability of the ciruit.
- 4A. Bandwidth of an amplifier lies between 150 Hz and 100 kHz. Find frequency range over which voltage gain is less than 2 dB from mid-band value.
- **4B.** Design an NMOS current mirror with  $V_{DD}=6V$ ,  $V_{SS}=0V$ ,  $I_{ref}=100\mu A$ . For the matched transistors L=10 $\mu$ m, W=100 $\mu$ m,  $V_{TH}=1V$ ,  $\mu_n C_{ox}=20\mu A/V^2$ .

- **4C.** For a class B Power amplifier providing a 20 V peak signal to a 8 Ω load (speaker) and a power supply of  $V_{CC}=|V_{EE}|=30$  V, determine the input power, output power and efficiency of the circuit.
- **5A.** State and prove Millers theorem for a BJT based amplifier circuit and derive suitable expression for the gain of the circuit.
- **5B.** Derive the expression for conversion efficiency of Class A series fed and transformer coupled Power amplifiers.
- **6A.** Classify the power amplifiers based on angle of conduction.
- **6B.** Write a note on series and shunt voltage regulators.
- 6C. Starting from 230 V, 50 Hz supply design a circuit to get an output of 5 V, 150 mA with ripple < 2%.</li>



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